### Notes:

Multiple problems (ones involving logical functions implementation and Verilog) have multiple correct answer. Only one example is shown below.

## Problem 1:

 $Y = \overline{(AB + C)D}$ 

One possible design with static CMOS gates,



This design uses 16 transistors.

The below is one design for a compound CMOS gate



This design uses 8 transistors

# Problem 2:

$$Y_{0} = \overline{A_{0}}(A_{1} + \overline{A_{2}})$$

$$Y_{1} = \overline{A_{0}} * \overline{A_{1}}$$

$$\overline{A_{2}}$$

$$Y_{0}$$

$$A_{0}$$

$$Y_{1}$$

## Problem 3:

For minimum sized 2 input NOR,

$$\begin{split} R_{SWN} &= 2k\Omega, R_{SWP} = 6k\Omega, C = 60 fF \\ T_{LH} &= 2*R_{SWP}*C = 12k*60f = 720*10^{-12} seconds = 720 pS \end{split}$$

# Problem 4:





Problem 5:



Middle stage can also be realize by splitting it into an inverter and a transmission gate

# Problem 6:



Problem 7:

Correct Diagram:



### **Problem 8:**

a)  $R_{W\_Aluminum} = \frac{2.8 \times 10^{-8}}{0.2 \times 10^{-6}} \times \frac{240}{5} + \frac{2.8 \times 10^{-8}}{0.2 \times 10^{-6}} \times \frac{40-5}{5} = 7.7\Omega$  $V_{wire} = 5 \times \frac{50}{50+7.7} = \frac{4.33 V}{5}$ 

b) 
$$R_{W_{Copper}} = 4.675 \ \Omega$$
  
 $V_{Resistor} = 5 * \left(\frac{50}{50+4.675}\right) = \frac{4.572 \ V}{4.572 \ V}$   
c)  $V_{RW} < 5V * 5\% = 0.25V$   
 $5V * \left(\frac{R_W}{50+R_W}\right) < 0.25V \rightarrow R_W < 2.632 \ \Omega$   
 $R_W = 7.7 * \frac{5\mu m}{Width_{wire}} \rightarrow Width_{Wire} \ge 14.63 \ \mu m$ 

## Problem 9:

Each inverter has  $C_L = 1.5 fF + 1.5 fF = 3fF$ total load capacitance C = 3 pF \* 6 = 18 fF $R_{SWp} = 6k\Omega \rightarrow T_{LH} = 6 k * 18 f = 108 * 10^{-12} s = 108 ps$ 

### Problem 10:

This is one simple implementation. The mux module and the test bench can be made in multiple ways.

Base Code:

Test bench Code:



Simulation results:

